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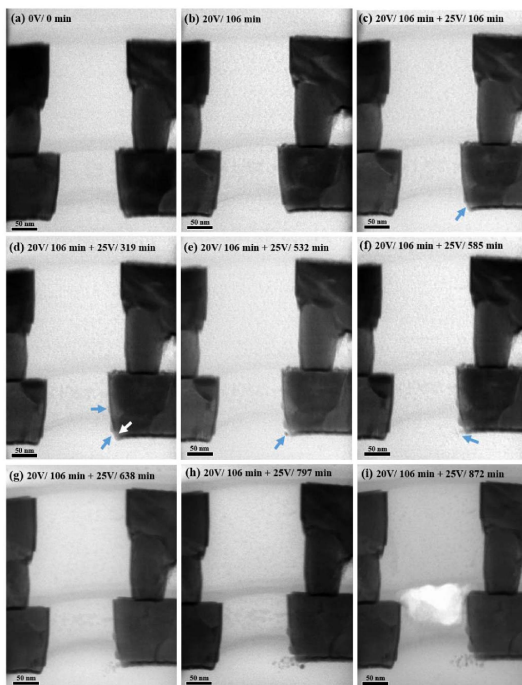
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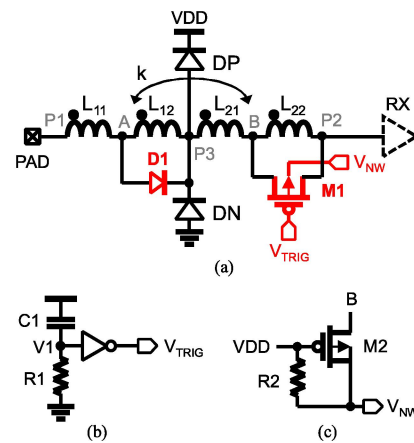
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SPECIAL SECTION ON STRESS-INDUCED PHENOMENA IN MICROELECTRONICS



Bright field scanning TEM image series from an in-situ experiment showing the time dependent dielectric breakdown (TDDB) in copper/low-k interconnect structures.

SPECIAL SECTION ON ESD DESIGN CHALLENGES FOR HIGH-SPEED APPLICATIONS



Schematic of the proposed T-coil with inductance-halving: (a) T-coil with a diode (D1) and a switch (M1), (b) trigger voltage generator, and (c) well-bias generator for M1.

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